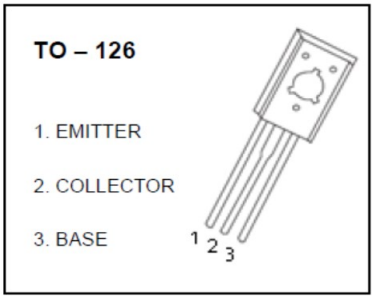
鼎德丰
DING DE FENG

PNP Epitaxial Silicon Transistor

BD442

FEATURES

- Complement to BD441
- Package:TO-126



ABSOLUTE MAXIMUM RATINGS

(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-4	A
Collector Peak Current	I_{CM}	-7	A
Base Current	I_B	-1	A
Collector Dissipation	P_C	1.25	W
Junction Temperature	Tj	150	℃
Storage Temperature	T_{STG}	- 55 ~ 150	℃

ELECTRICAL CHARACTERISTICS

(Ta = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=-0.1mA，I_E=0	-80		V
Collector-emitter sustaining voltage	$V_{CEO(SUS)}$	I_C=-100mA，I_B=0	-80		V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-0.1mA,I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-80V I_E=0		-0.1	mA
Collector cut-off current	I_{CES}	V_{CB}=-80V, V_{BE} =0		-0.1	mA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0		-1	mA
DC current gain	H_{FE1}	V_{CE}=-1V ,I_C=-500mA	40	140	
	H_{FE2}	V_{CE}=-5V ,I_C=-10mA	15		
	H_{FE3}	V_{CE}=-1V ,I_C=-2A	15		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-2A ,I_B=-200mA		-0.8	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V,I_C=-2A		-1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}=-1V,I_C=-250mA	3		MHz